

## High Power SP4T Switch with Logic Control

### Description

This IC can be used in wireless communication systems, for example, W-CDMA handsets.

The IC has on-chip logic for operation with 5 CMOS control inputs.

The Sony JPHEMT process is used for low insertion loss and on-chip logic circuit.

### Features

- Low insertion loss
- 5 CMOS compatible control line
- Small package size: 20-pin UQFN

### Applications

Antenna switch for cellular handsets  
W-CDMA

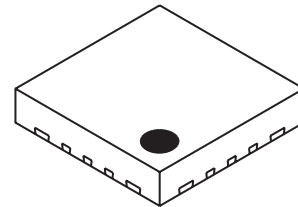
### Structure

GaAs JPHEMT MMIC

### Absolute Maximum Ratings (Ta = 25°C)

- |                         |                  |             |    |
|-------------------------|------------------|-------------|----|
| • Bias voltage          | V <sub>DD</sub>  | 7           | V  |
| • Control voltage       | V <sub>ctl</sub> | 5           | V  |
| • Operation temperature | T <sub>opr</sub> | -35 to +85  | °C |
| • Storage temperature   | T <sub>stg</sub> | -65 to +150 | °C |

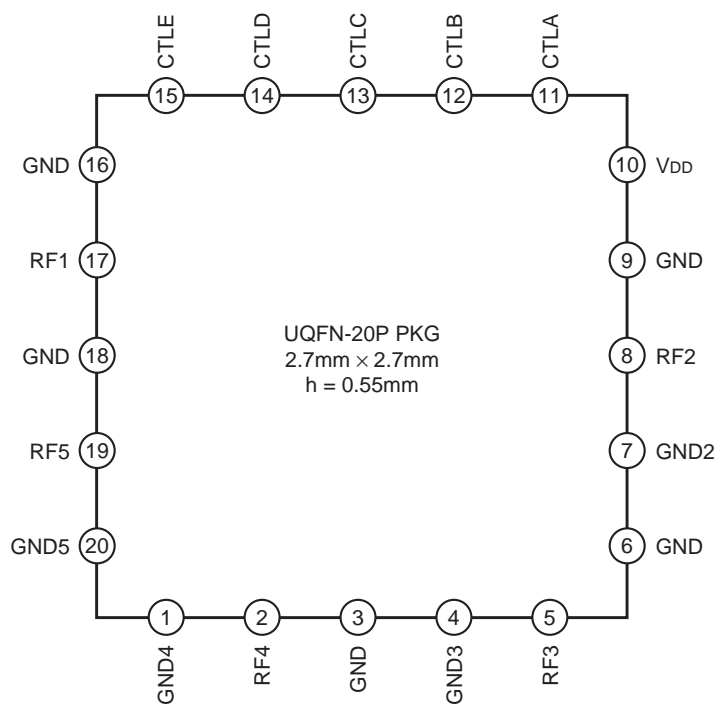
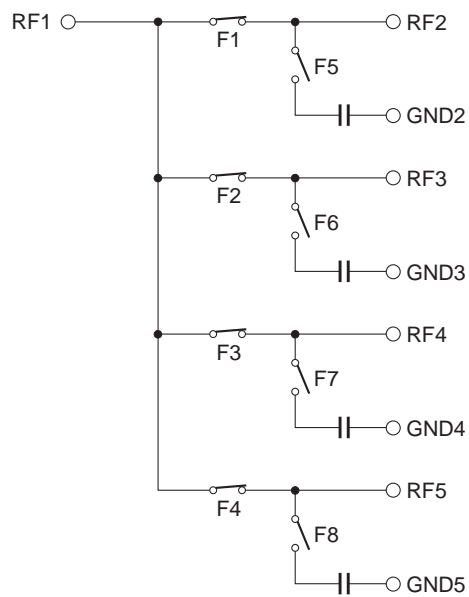
20 pin UQFN (Plastic)



GaAs MMIC's are ESD sensitive devices. Special handling precautions are required.

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Block Diagram and Recommended Circuit



**Truth Table**

State	ON Pass	CTLA	CTLB	CTLC	CTLD	CTLE	F1	F2	F3	F4	F5	F6	F7	F8
1	RF1 – RF2	H H H	H/L H L	H H L	L L H	L H L	ON	OFF	OFF	OFF	OFF	ON	ON	ON
2	RF1 – RF3	H H	H L	L L	H/L H/L	H/L H	OFF	ON	OFF	OFF	ON	OFF	ON	ON
3	RF1 – RF4	H H H	H/L L L	H H L	H L L	H/L H L	OFF	OFF	ON	OFF	ON	ON	OFF	ON
4	RF1 – RF5	L	H/L	H/L	H/L	H/L	OFF	OFF	OFF	ON	ON	ON	ON	OFF

**DC Bias Condition**

(Ta = 25°C)

Item	Min.	Typ.	Max.	Unit
Vctl (H)	2.0	2.85	3.6	V
Vctl (L)	0	—	0.4	V
VDD	2.5	2.85	3.6	V

Electrical Characteristics

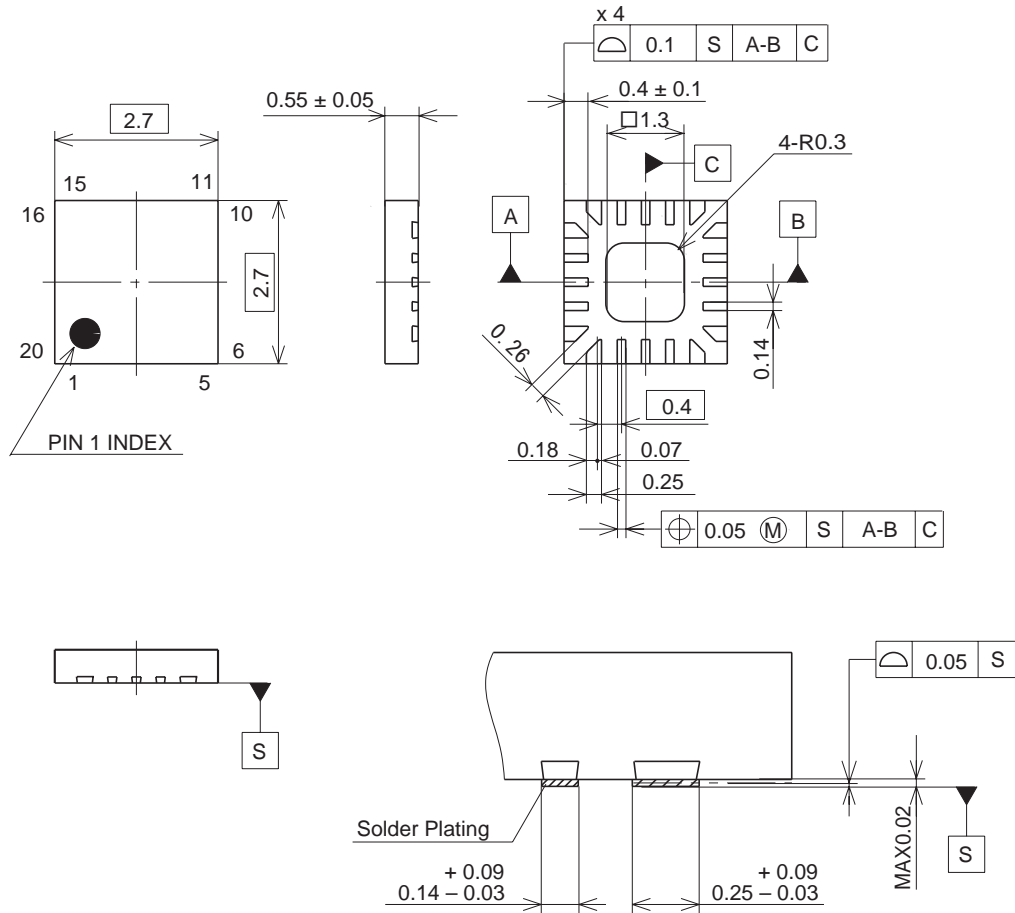
(Ta = 25°C)

Item	Symbol	State	Condition	Min.	Typ.	Max.	Unit
Insertion loss	IL	1	RF1 – RF2, 1920 to 1980MHz		0.35	0.60	dB
			2110 to 2170MHz		0.40	0.65	dB
		2	RF1 – RF3, 1920 to 1980MHz		0.35	0.60	dB
			2110 to 2170MHz		0.40	0.65	dB
		3	RF1 – RF4, 1920 to 1980MHz		0.35	0.60	dB
			2110 to 2170MHz		0.40	0.65	dB
		4	RF1 – RF5, 1920 to 1980MHz		0.80	1.10	dB
			2110 to 2170MHz		0.85	1.15	dB
Isolation	ISO.	2, 3	RF1 – RF2, 1920 to 2170MHz	30	35		dB
		1, 3	RF1 – RF3, 1920 to 2170MHz	30	35		dB
		1, 2	RF1 – RF4, 1920 to 2170MHz	30	35		dB
		1, 2, 3	RF1 – RF5, 1920 to 2170MHz	20	25		dB
		4	RF1 – RF2, 3, 4, 1920 to 2170MHz	25	30		dB
VSWR	VSWR		50Ω		1.2		—
Switching speed	TSW				4	10	μs
ACLR	ACLR1		±5MHz, 3.84MHz BW, *1		-60	-50	dBc
	ACLR2		±10MHz, 3.84MHz BW, *1		-62	-55	dBc
Harmonics	2fo		*1		-75	-60	dBc
	3fo		*1		-75	-60	dBc
Bias current	I <sub>DD</sub>		V <sub>DD</sub> = 2.85V		0.20	0.35	mA
Control current	I <sub>ctl</sub>		V <sub>ctl</sub> (H) = 2.85V		15	25	μA

\*1 Pin = 25dBm, 0/2.85V control, V<sub>DD</sub> = 2.85V, 1920 to 1980MHz

Package Outline Unit: mm

20PIN UQFN (PLASTIC)



TERMINAL SECTION

Note: Cutting burr of lead are 0.05mm MAX.

SONY CODE	UQFN-20P-01
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.02g

LEAD PLATING SPECIFICATIONS

ITEM	SPEC.
LEAD MATERIAL	COPPER ALLOY
SOLDER COMPOSITION	Sn-Bi Bi:1-4wt%
PLATING THICKNESS	5-18µm